TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

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LOW-VOLTAGE OCTAL BUS BUFFER WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

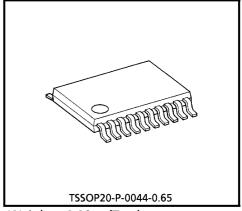
The TC74VCX2244FT is a high performance CMOS OCTAL BUS BUFFER. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This device is non-inverting 3 - state buffer having four active-low output enables. When the \overline{OE} input is high, the outputs are in a high impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The 26- Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.08 g (Typ.)

FEATURES

26- Ω Series Resistors on Outputs.

Low Voltage Operation : $V_{CC} = 1.8 \sim 3.6 \text{ V}$

High Speed Operation : $t_{pd} = 4.4 \text{ ns (max)}$ at $V_{CC} = 3.0 \sim 3.6 \text{ V}$

: $t_{pd} = 5.6 \text{ ns (max)}$ at $V_{CC} = 2.3 \sim 2.7 \text{ V}$

: $t_{pd} = 9.8 \text{ ns (max)}$ at $V_{CC} = 1.8 \text{ V}$

3.6 V Tolerant inputs and outputs.

Output Current $: I_{OH}/I_{OL} = \pm 12 \text{ mA (min) at } V_{CC} = 3.0 \text{ V}$

: $I_{OH}/I_{OL} = \pm 8 \text{ mA (min)}$ at $V_{CC} = 2.3 \text{ V}$

: $I_{OH}/I_{OL} = \pm 4 \text{ mA (min)}$ at $V_{CC} = 1.8 \text{ V}$

: ±300 mA Latch-up Performance

ESD Performance : Human Body Model > ±2000 V

: Machine Model > ±200 V

Package

(Thin Shrink Small Outline Package)

- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (Note 1)

(Note 1): To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

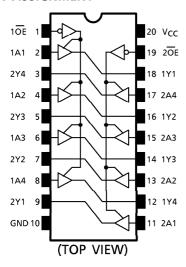
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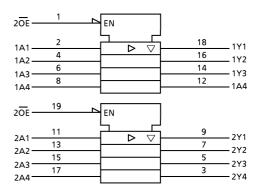
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PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

INP	UTS	OUTPUTS
ŌĒ	An	0011013
L	L	L
L	Н	Н
Н	Х	Z

X : Don't Care Z : High Impedance

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT	
Power Supply Voltage	V _{CC}	-0.5~4.6	V	
DC Input Voltage	VIN	-0.5~4.6	V	
DC Output Voltage	\/ - · · =	-0.5~4.6 (Note 1)	V	
DC Output Voltage	Vout	-0.5~V _{CC} + 0.5 (Note 2)] '	
Input Diode Current	lικ	– 50	mA	
Output Diode Current	lok	± 50 (Note 3)	mA	
DC Output Current	lout	± 50	mA	
Power Dissipation	PD	180	mW	
DC V _{CC} / Ground Current	ICC/IGND	± 100	mA	
Storage Temperature	T _{stg}	-65∼150	°C	

(Note 1) : Off-State

(Note 2) : High or Low State. $I_{\mbox{OUT}}$ absolute maximum rating must be observed.

(Note 3) : $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	L RATING	
Summit Valtana	V	1.8~3.6	V
Supply Voltage	VCC	1.2~3.6 (Note 4)	V
Input Voltage	VIN	-0.3~3.6	V
Output Voltage	\/ - · · -	0~3.6 (Note 5)	V
	Vout	0~ V _{CC} (Note 6)	V
		± 12 (Note 7)	
Output Current	I _{OH} /I _{OL}	±8 (Note 8)	mΑ
		±4 (Note 9)	
Operating Temperature	Topr	- 40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns / V

(Note 4) : Data Retention Only

(Note 5) : Off-State

(Note 6): High or Low State (Note 9): V_{CC} = $3.0 \sim 3.6 \text{ V}$ (Note 8): V_{CC} = $2.3 \sim 2.7 \text{ V}$ (Note 9): V_{CC} = 1.8 V(Note 10): V_{IN} = $0.8 \sim 2.0 \text{ V}$, V_{CC} = 3.0 V

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40\sim85^{\circ}$ C, 2.7 V < V_{CC} \leq 3.6 V)

PARA	METER	SYMBOL	TEST	CONDITION	V _{CC} (V)	MIN	MAX	UNIT
Input	"H" Level	VIH			2.7~3.6	2.0	_	V
Voltage	"L" Level	V_{IL}			2.7~3.6	_	0.8	· ·
			.,	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2		
	"H" Level	Voн	V _{IN} =	$I_{OH} = -6 \text{mA}$	2.7	2.2	_	
044		J.,	V _{IH} or V _{IL}	I _{OH} = -8 mA	3.0	2.4	_	
Output				I _{OH} = -12 mA	3.0	2.2	_	V
Voltage			V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7~3.6	_	0.2	
	"L" Level	V _{OL}		I _{OL} = 6 mA	2.7	_	0.4	
	L Level			I _{OL} = 8 mA	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8	
Input Leaka	ge Current	IN	$V_{IN} = 0 \sim 3$.	6 V	2.7~3.6	_	± 5.0	μ A
3-State Out Off-State Co	urrent	loz	V _{IN} = V _{IH} · V _{OUT} = 0~		2.7~3.6	_	± 10.0	μ A
Power Off I Current	Leakage	lOFF	V _{IN} , V _{OUT}	= 0~3.6 V	0	_	10.0	μΑ
Quiescent S	upply	laa	$V_{IN} = V_{CC}$	or GND	2.7~3.6	_	20.0	^
Current		lcc	$V_{CC} \leq (V_{IN})$	$V_{OUT} \leq 3.6 V$	2.7~3.6	_	± 20.0	μ A
Increase In Input	ICC Per	ΔΙCC	V _{IH} = V _{CC}	- 0.6 V	2.7~3.6	_	750	μ A

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40\sim85^{\circ}$ C, 2.3 V \leq V_{CC} \leq 2.7 V)

PARA	METER	SYMBOL	TEST	CONDITION	V _{CC} (V)	MIN	MAX	UNIT														
Input	"H" Level	V_{IH}			2.3~2.7	1.6	_	V														
Voltage	"L" Level	V _{IL}			2.3~2.7	_	0.7	· ·														
			.,	I _{OH} = -100 μA	2.3~2.7	V _C C - 0.2																
	"H" Level	Voн	V _{IN} =	$I_{OH} = -4 \text{mA}$	2.3	2.0																
Output			V _{IH} or V _{IL}	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	VIH or VIL	I _{OH} = -6 mA	2.3	1.8	_	_ ,
Voltage				I _{OH} = -8 mA	2.3	1.7		V														
			VIII or VII	I _{OL} = 100 μA	2.3~2.7	_	0.2															
	"L" Level	v_{OL}								IOL = 6 mA	2.3	_	0.4									
				IOL = 8 mA	2.3	_	0.6															
Input Leak	age Current	ΙΝ	$V_{IN} = 0 \sim 3$.	6 V	2.3~2.7	_	± 5.0	μ A														
3-State Out Off-State C		loz	V _{IN} = V _{IH} V _{OUT} = 0~	or V _{IL} -3.6 V	2.3~2.7	_	± 10.0	μΑ														
Power Off Current	Leakage	lOFF	VIN, VOUT	= 0~3.6 V	0		10.0	μΑ														
Quiescent S	Supply	laa	$V_{IN} = V_{CC}$	or GND	2.3~2.7		20.0															
Current		lcc	$V_{CC} \leq (V_{IN})$, V _{OUT}) ≦ 3.6 V	2.3~2.7		± 20.0	μ A														

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = $-40\sim85^{\circ}$ C, 1.8 V \leq V_{CC} < 2.3 V)

PARA	METER	SYMBOL	TEST	CONDITION	V _{CC} (V)	MIN	MAX	UNIT
Input	"H" Level	V _{IH}			1.8~2.3	0.7 × V _{CC}		V
Voltage	"L" Level	V _{IL}			1.8~2.3	-	0.2 × V _{CC}	V
Output	"H" Level	Voн	V _{IN} =	I _{OH} = -100 μA	1.8	V _C C - 0.2		
Output Voltage	ut		VOH VIH or VIL	$I_{OH} = -4 \text{mA}$	1.8	1.4	_	V
Voltage	"L" Level	\/ a .	V _{IN} =	I _{OL} = 100 μA	1.8	_	0.2	
	L Levei	V_{OL}	V _{IH} or V _{IL}	I _{OL} = 4 mA	1.8	_	0.3	
Input Leak	age Current	IN	$V_{IN} = 0 \sim 3$.	6 V	1.8	_	± 5.0	μΑ
3-State Out Off-State C		loz	V _{IN} = V _{IH} (V _{OUT} = 0~		1.8	_	± 10.0	μΑ
Power Off Current	Leakage	lOFF	V _{IN} , V _{OUT}	= 0~3.6 V	0	_	10.0	μΑ
Quiescent S	Quiescent Supply			V _{IN} = V _{CC} or GND		_	20.0	.,Λ
Current		lcc	$V_{CC} \leq V_{IN}$, V _{OUT}) ≦ 3.6 V	1.8		± 20.0	μ A

AC characteristics (Ta = $-40\sim85^{\circ}$ C, Input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN	MAX	UNIT
	4		1.8	1.5	9.8	
Propagation Delay Time	t _{pLH}	(Fig.1, 2)	2.5 ± 0.2	0.8	5.6	ns
	t_pHL		3.3 ± 0.3	0.6	4.4	
2 State Output Enable	+		1.8	1.5	9.8	
3-State Output Enable Time	t _{pZL}	(Fig.1, 3)	2.5 ± 0.2	0.8	6.5	ns
Time	t _{pZH}		3.3 ± 0.3	0.6	5.0	
3-State Output Disable	+		1.8	1.5	7.2	
Time	t _{pLZ}	(Fig.1, 3)	2.5 ± 0.2	0.8	4.0	ns
Time	t _{pHZ}		3.3 ± 0.3	0.6	3.6	
Output To Output Skew	+		1.8	_	0.5	
	^t osLH ^t osHL	(Note 11)	2.5 ± 0.2	_	0.5	ns
			3.3 ± 0.3	_	0.5	

For $C_L = 50 \, pF$, add approximately 300 ps to the AC maximum specification.

(Note 11) : Parameter guaranteed by design.
$$(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, \ t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$$

PARAMETER	SYMBOL	TEST CONDITIO	ON	V _{CC} (V)	TYP.	UNIT
Quiet Quitnut Maximum		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note 12)	1.8	0.15	
Quiet Output Maximum Dynamic VOI	V _{OLP}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note 12)	2.5	0.25	V
Dynamic vOL		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 12)	3.3	0.35	
Quiet Qutnut Minimum		V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 12)	1.8	- 0.15	
Quiet Output Minimum Dynamic V _{OL}	VOLV	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note 12)	2.5	-0.25	V
Dynamic VOL		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 12)	3.3	- 0.35	
Quiet Output Minimum Dynamic V _{OH}		V _{IH} = 1.8 V, V _{IL} = 0 V	(Note 12)	1.8	1.55	
	VOHV	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note 12)	2.5	2.05	V
Dynamic VOH		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note 12)	3.3	2.65	

(Note 12): Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP.	UNIT
Input Capacitance	CIN		1.8, 2.5, 3.3	6	рF
Output Capacitance	COUT		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C _{PD}	$f_{IN} = 10 MHz$ (Note 13)	1.8, 2.5, 3.3	20	рF

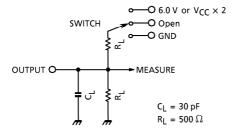
(Note 13): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

ICC (opr.) = CpD · VCC · flN + ICC / 8 (per bit)

TEST CIRCUIT

Fig.1



PARAMETER	SWITCH
t _{pLH} , t _{pHL}	Open
t _{pLZ} , t _{pZL}	6.0 V @V _{CC} = $3.3 \pm 0.3 \text{ V}$ V _{CC} × 2 @V _{CC} = $2.5 \pm 0.2 \text{ V}$ @V _{CC} = 1.8 V
t _{pHZ} , t _{pZH}	GND

AC WAVEFORM

Fig.2 t_{pLH} , t_{pHL}

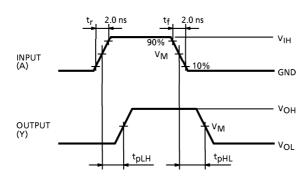
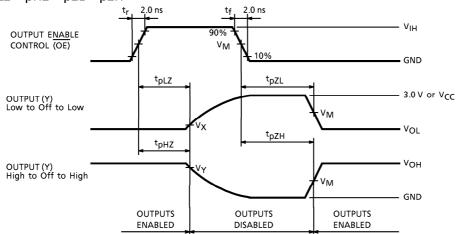


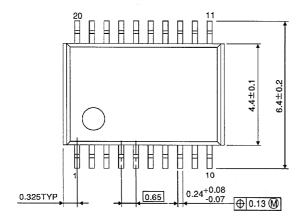
Fig.3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

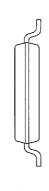


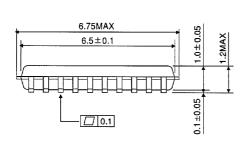
SYMBOL	V _{CC}					
STIVIBOL	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V			
V_{IH}	2.7 V	V _{CC}	VCC			
٧ _M	1.5 V	V _{CC} /2	V _{CC} /2			
Vχ	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V			
VY	V _{OH} – 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V			

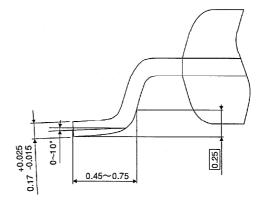
OUTLINE DRAWING TSSOP20-P-0044-0.65

Unit: mm









Weight: 0.08 g (Typ.)

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